Claims

[Claim 1]

A polycrystalline silicon rod comprising:

a core wire formed of silicon, wherein

a total metal concentration of iron and nickel is 40 pptw or less in terms of elements in a region within 2 mm from an interface between the core wire and polycrystalline silicon deposited on a surface of the core wire.

[Claim 2]

The polycrystalline silicon rod according to claim 1, wherein

in the region, an iron concentration is 20 pptw or less in terms of elements, and a nickel concentration is 5 pptw or less in terms of elements.

[Claim 3]

The polycrystalline silicon rod according to claim 1 or 2, wherein

in the region, a chromium concentration is 10 pptw or less in terms of elements.

~~[Claim 4]~~

~~A method for producing a polycrystalline silicon rod, comprising:~~

~~using a reactor including a bottom plate provided with electrodes for energizing a core wire formed of silicon and a domical cover covering the bottom plate; and~~

~~while the core wire is connected to the electrodes and energized, supplying a polycrystalline silicon deposition raw material gas into the reactor so as to perform gas phase growth of polycrystalline silicon on a surface of the core wire, wherein~~

~~during a period from a completion of cleaning of the surface of the core wire to a connection of the core wire to the electrodes and covering of the bottom plate with the cover from an upper portion of the core wire, the silicon core wire is placed in an atmosphere adjusted to a cleanliness of Class 4 to Class 6 as defined in ISO 14644-1.~~